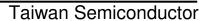
## MBRF835CT - MBRF8150CT



# 8A, 35V - 150V Schottky Barrier Rectifier

### FEATURES

TAIWAN

• AEC-Q101 qualified available

EMICONDUCTOR

- Low power loss, high efficiency
- Guard ring for overvoltage protection
- High surge current capability
- UL Recognized File # E-326243
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

### **APPLICATIONS**

- Switching mode power supply (SMPS)
- Adapters
- DC to DC converters

### **MECHANICAL DATA**

- Case: ITO-220AB
- Molding compound meets UL 94V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Mounting torque: 0.56 N⋅m maximum
- Meet JESD 201 class 2 whisker test
- Polarity: As marked
- Weight: 1.70g (approximately)

KEY PARAMETERS			
PARAMETER	VALUE	UNIT	
I <sub>F</sub>	8	А	
V <sub>RRM</sub>	35 - 150	V	
I <sub>FSM</sub>	150	А	
T <sub>J MAX</sub>	150	°C	
Package	ITO-220AB		
Configuration	Dual dies		





PIN1 O	ן PIN2
	<u> </u>
PIN3 O	Cathode

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted)									
		MBRF	MBRF	MBRF	MBRF	MBRF	MBRF	MBRF	
PARAMETER	SYMBOL	835	845	850	860	890	8100	8150	UNIT
		СТ	СТ	СТ	СТ	СТ	СТ	СТ	
		MBRF	MBRF	MBRF	MBRF	MBRF	MBRF	MBRF	
Marking code on the device		835	845	850	860	890	8100	8150	
		СТ	СТ	СТ	СТ	СТ	СТ	СТ	
Repetitive peak reverse voltage	$V_{RRM}$	35	45	50	60	90	100	150	V
Reverse voltage, total rms value	V <sub>R(RMS)</sub>	24	31	35	42	63	70	105	V
Forward current	I <sub>F</sub>				8				А
Surge peak forward current, 8.3ms single half sine wave superimposed on rated load	I <sub>FSM</sub>				150				A
Critical rate of rise of off-state voltage	dv/dt				10,000				V/µs
Junction temperature	T <sub>J</sub> -55 to +150		°C						
Storage temperature	T <sub>STG</sub>			-{	55 to +15	50			°C



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THERMAL PERFORMANCE			
PARAMETER	SYMBOL	ТҮР	UNIT
Junction-to-case thermal resistance	R <sub>eJC</sub>	6	°C/W

ELECTRICAL SPECIFICATIONS (T <sub>A</sub> = 25°C unless otherwise noted)						
PARAMETER		CONDITIONS	SYMBOL	ТҮР	MAX	UNIT
	MBRF835CT			-	0.55	V
	MBRF845CT					
(1)	MBRF850CT			-	0.70	V
Forward voltage per diode <sup>(1)</sup>	MBRF860CT	$I_F = 4A, T_J = 25^{\circ}C$	VF			
	MBRF890CT			-	0.85	v
	MBRF8100CT				0.00	v
	MBRF8150CT			-	0.95	V
	MBRF835CT	T <sub>J</sub> = 25°C				
	MBRF845CT		- I <sub>R</sub>			
	MBRF850CT					
	MBRF860CT			-	100	μA
	MBRF890CT					
	MBRF8100CT					
Reverse current @ rated $V_R$ per	MBRF8150CT					
diode <sup>(2)</sup>	MBRF835CT			_	15	mA
	MBRF845CT	T <sub>J</sub> = 125°C		_	15	
	MBRF850CT				10	mA
	MBRF860CT			-	10	ША
	MBRF890CT					
	MBRF8100CT			-	5	mA
	MBRF8150CT					

#### Notes:

1. Pulse test with PW = 0.3ms

2. Pulse test with PW = 30ms

ORDERING INFORMATION		
ORDERING CODE <sup>(1)(2)</sup>	PACKAGE	PACKING
MBRF8xCT	ITO-220AB	50 / Tube
MBRF8xCTH	ITO-220AB	50 / Tube

Notes:

1. "x" defines voltage from 35V(MBRF835CT) to 150V(MBRF8150CT)

2. "H" means AEC-Q101 qualified



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### **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

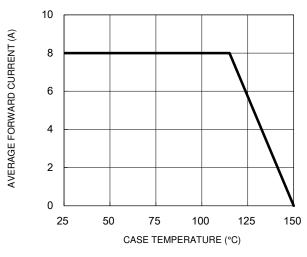
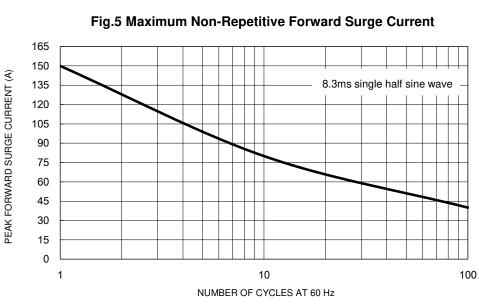


Fig.1 Forward Current Derating Curve

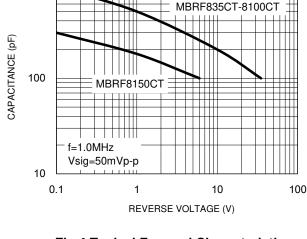
## **Fig.3 Typical Reverse Characteristics**

100 INSTANTANEOUS FORWARD CURRENT (A) 10 INSTANTANEOUS REVERSE CURRENT (mA) MBRF835CT-845CT MBRF850CT-860CT T,⊨125°C 10 1 , ,=75<sup>°</sup>C MBRF8150CT 0.1 1 MBRF890CT-8100CT T<sub>.I</sub>=25°C Pulse width 300µs 1% duty cycle 0.01 0.1 10 20 30 40 50 60 70 80 100 90 0.1 0.3 0.9 1.3 0.5 0.7 1.1 PERCENT OF RATED PEAK REVERSE VOLTAGE (%) FORWARD VOLTAGE (V)

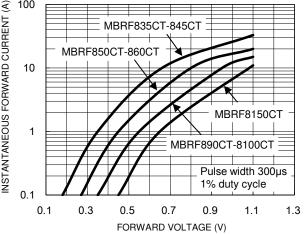


**Fig.2 Typical Junction Capacitance** 

1000



**Fig.4 Typical Forward Characteristics** 

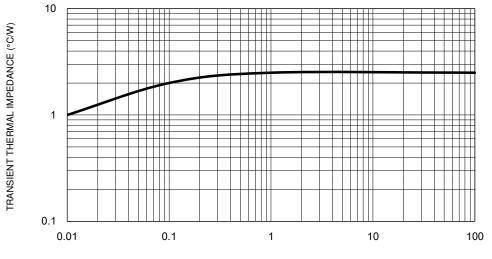




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### **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 



### Fig.6 Typical Transient Thermal Impedance

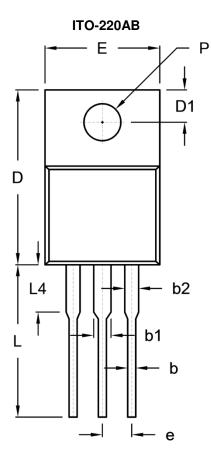
PULSE DURATION (s)

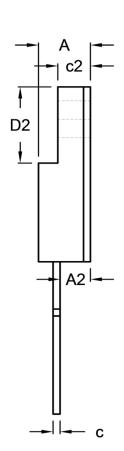


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### PACKAGE OUTLINE DIMENSIONS





DIM.	Unit (mm)		Unit	(inch)
	Min.	Max.	Min.	Max.
A	4.30	4.70	0.169	0.185
A2	2.30	2.96	0.091	0.117
b	0.50	0.90	0.020	0.035
b1	-	1.80	-	0.071
b2	0.95	1.45	0.037	0.057
с	0.46	0.76	0.018	0.030
c2	2.50	3.16	0.098	0.124
D	14.80	15.50	0.583	0.610
D1	2.40	3.20	0.094	0.126
D2	6.30	6.90	0.248	0.272
E	9.60	10.30	0.378	0.406
е	2.41	2.67	0.095	0.105
L	12.60	13.80	0.496	0.543
L4	-	4.10	-	0.161
Р	3.00	3.40	0.118	0.134

### **MARKING DIAGRAM**

雪別 GYWWF
P/N
<b>→</b> + • + •

P/N	= Marking Code
G	= Green Compound
YWW	= Date Code
F	= Factory Code



## MBRF835CT - MBRF8150CT

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